Powerex, Inc., 173 Pavilion Lane, Youngwood, Pennsylvania 15697 (724) 925-7272
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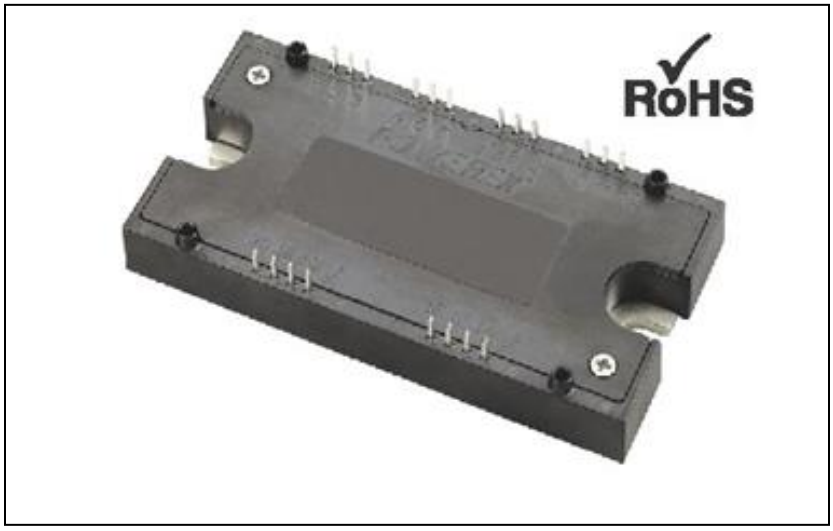
Silicon Carbide
Dual MOSFET Module
180 Amperes / 1200 Volts / 13 mΩ



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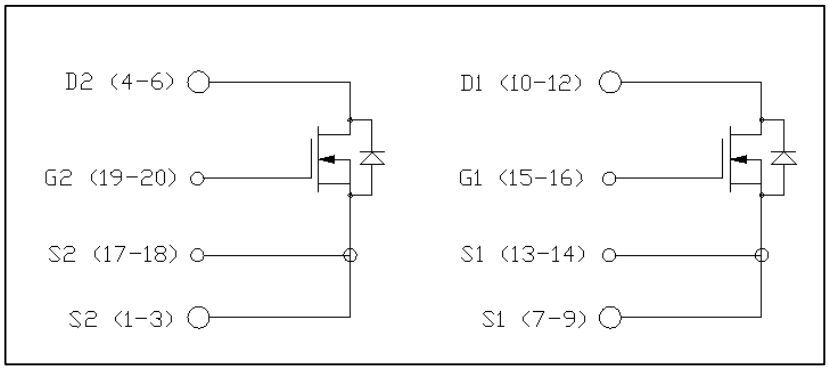

Description:
Powerex Silicon Carbide MOSFET Modules are designed for use in high frequency applications. Each module consists of two MOSFET Silicon Carbide Transistors with each transistor having a reverse connected super-fast recovery free-wheel silicon carbide Schottky diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:
☐ Junction Temperature: 175°C
☐ Industry Leading $R_{DS(on)}$
☐ High Speed Switching
☐ Low Switching Losses
☐ Low Capacitance
☐ Low Drive Requirement
☐ High Power Density
☐ Zero Reverse Recovery from Diode
☐ Isolated Baseplate
☐ Aluminum Nitride Isolation

Applications:
☐ Energy Saving Power Systems
☐ High Frequency Type Power Systems
☐ High Temperature Power Systems

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Absolute Maximum Ratings, T_j = 25°C unless otherwise specified

Characteristics	Symbol	QJD1218SA1	Units
Drain-Source Voltage (G-S Short)	V_{DSS}	1200	Volts
Gate-Source Voltage, DC, D-S short	V_{GSS}	0 / +22	Volts
Gate-Source Voltage, pulse, repetitive	V_{GSS}	-5 / +22	Volts
Drain Current (Continuous) at T_C=61°C*1	I_D	180	Amperes
Drain Current (Pulse, Repetitive)*2 , T_{vj}=150°C*3	$I_{D(pulse)}$	360	Amperes
Maximum Power Dissipation (T_C=25°C, T_J< 175°C) *1	P_D	681	Watts
Maximum Junction Temperature	$T_{J\,max}$	175	°C
Operating Junction Temperature, Continuous operation (under switching)	$T_{j\,op}$	-40 to 150	°C
Maximum Case Temperature*1	$T_{c\,max}$	125	°C
Storage Temperature	T_{stg}	-40 to 125	°C
Mounting Torque, M6 Mounting Screws	—	5	N-m
Module Weight (Typical)	—	270	Grams
Isolation Voltage	V_{ISO}	3500	Volts

*1 Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink under the chips.
*2 Pulse width and repetition rate should be such that device junction temperature (T_J) does not exceed $T_{J\,(MAX)}$ rating.
*3 Junction temperature (T_{vj}) should not increase beyond $T_{J\,(MAX)}$ rating.

DC Characteristics, T_J=25°C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain Source Leakage Current	I_{DSS}	V_{DS}=1200V, V_{GS}=0V	-	-	1.2	mA
Gate Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=15V	-	-	1000	nA
Gate Source Threshold Voltage	$V_{GS(th)}$	V_{DS}=10V, I_D=9mA	3.6	4.6	5.6	Volts
Drain Source On-Resistance (chip)	$R_{DS(on)}$	V_{GS}=15V I_D=180A	6.7	13	18.4	mΩ
		T_J=150°C	-	14.7	-	mΩ
Internal Gate Source Series Resistance	R_g	Per Switch	-	1.0	-	Ω
Stray Inductance	L_s	P-N	-	10	-	nH

Dynamic Characteristics, T_J=25°C unless otherwise specified

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Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ISS}	V_{GS}=0V, V_{DS}=10V	-	12	-	nF
Output Capacitance	C_{OSS}		-	9.8	-	nF
Reverse Transfer Capacitance	C_{RSS}		-	330	-	pF
Turn-On Delay Time	$t_{D(on)}$	V_{DD}=600V, V_{GS}= ±15V I_D=180A, R_G=1Ω, T_J=150°C Inductive Load, per Pulse	-	35	-	ns
Rise Time	t_R		-	20	-	ns
Turn-Off Delay Time	$t_{D(off)}$		-	65	-	ns
Fall Time	t_F		-	15	-	ns
Turn-On Energy	E_{on}	V_{DD}=600V, V_{GS}= ±15V I_D=180A, R_G=1Ω, T_J=150°C Inductive Load, per Pulse	-	9.9	-	mJ
Turn-Off Energy	E_{off}		-	5.4	-	mJ
Total Gate Charge	Q_G	V_{DD}=600V, V_{GS}=0 to 15V I_D=180A, T_j=25°C	-	386	-	nC

Anti-parallel Diode, T_J=25°C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Diode Forward Voltage	V_{SD}	V_{GS}=-15V I_S=180A	-	1.53	-	V
		T_J=150°C	-	2.05	-	V

Thermal Resistance Characteristics

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per MOSFET	-	-	0.34	°C/W
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per Diode	-	-	0.31	°C/W
Contact Thermal Resistance	$R_{th(c-s)}$	Per ½ Module, Thermal Grease Applied	-	0.04	-	°C/W

NTC Thermistor Part

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Zero Power Resistance	R_{25}	T_C=25°C	4.85	5.00	5.15	kΩ
Deviation of Resistance	ΔR/R	T_C=100°C, R_{100}=493Ω	-7.3	-	+7.8	%
B constant	$B_{(25/50)}$	$B_{(25/50)}=\ln(R_{25}/R_{50}) / (1/T_{25} - 1/T_{50})$*4	__	3375	__	K
Power Dissipation	P_{25}	T_C=25°C	__	__	10	mW

*4 R25: Resistance at Absolute Temperature T25 (K), R50: Resistance at Absolute Temperature T50 (K), T25 = 25(°C) + 273.15 = 298.15(K), T50 = 50(°C) + 273.15 = 323.15(K)

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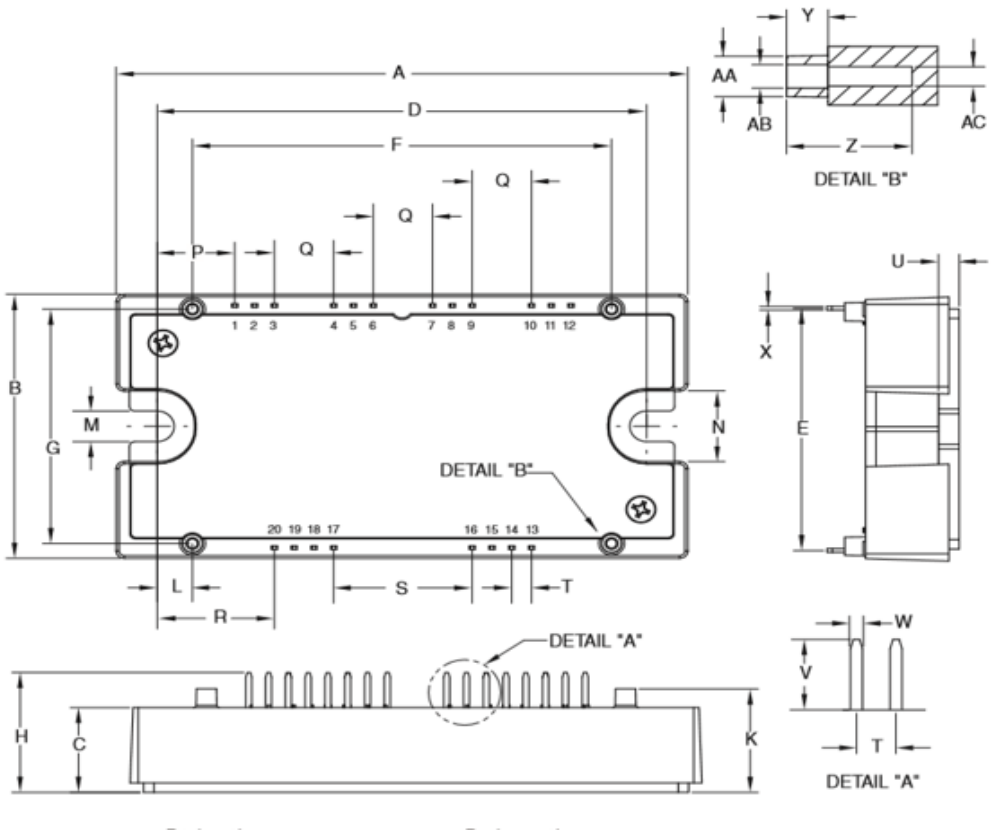

Dimensions	Inches	Millimeters
A	4.32	109.8
B	2.21	56.1
C	0.71	18.0
D	3.70±0.02	94.0±0.5
E	2.026	51.46
F	3.17	80.5
G	1.96	49.8
H	1.00	25.5
K	0.87	22.0
L	0.266	6.75
M	0.26	6.5
N	0.59	15.0
P	0.586	14.89

Dimensions	Inches	Millimeters
Q	0.449	11.40
R	0.885	22.49
S	1.047	26.6
T	0.15	3.80
U	0.16	4.0
V	0.30	7.5
W	0.045	1.15
X	0.03	0.8
Y	0.16	4.0
Z	0.47	12.1
AA	0.17 Dia.	4.3 Dia.
AB	0.10 Dia.	2.5 Dia.
AC	0.08 Dia.	2.1 Dia.